



BT151 12A SCR

Rev.A.1.0

DESCRIPTION:

With high ability to withstand the shock loading of large current, BT151 of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220B is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
I		

BT151

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

MARKING

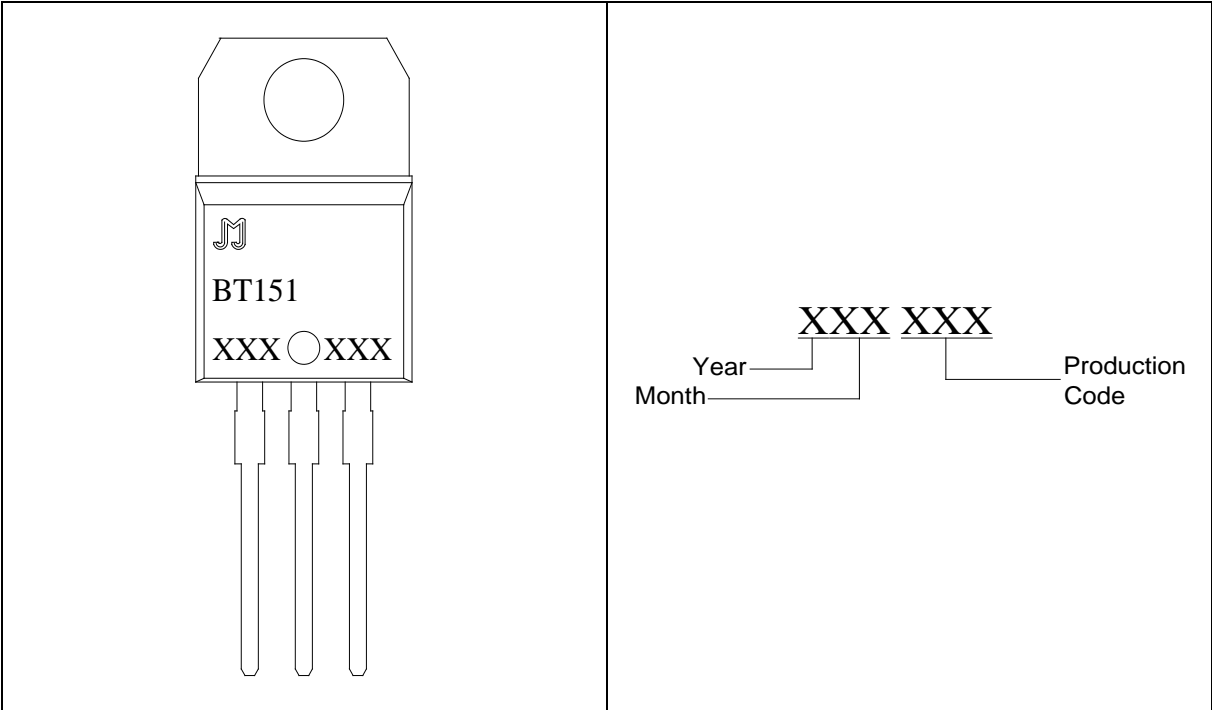


FIG.1 Maximum power dissipation versus RMS on-state current

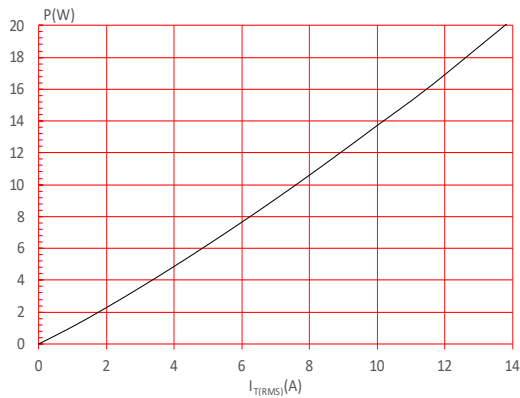


FIG.2: RMS on-state current versus case temperature

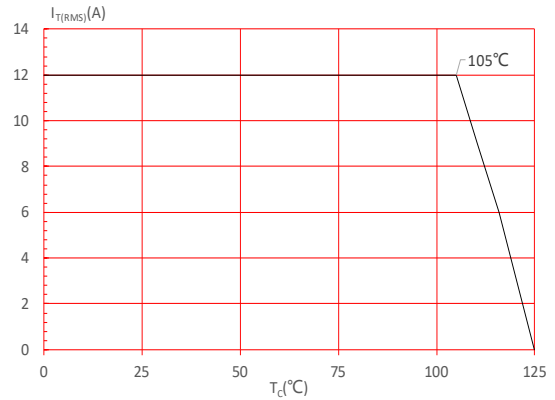


FIG.3: Surge peak on-state current versus number of cycles

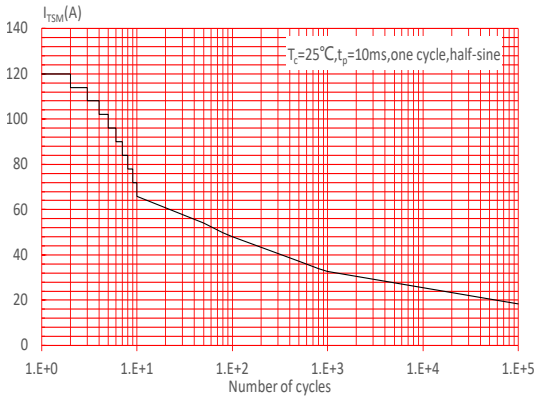


FIG.4: On-state characteristics

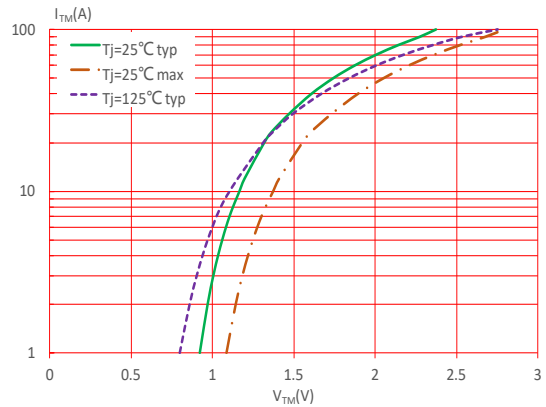


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t

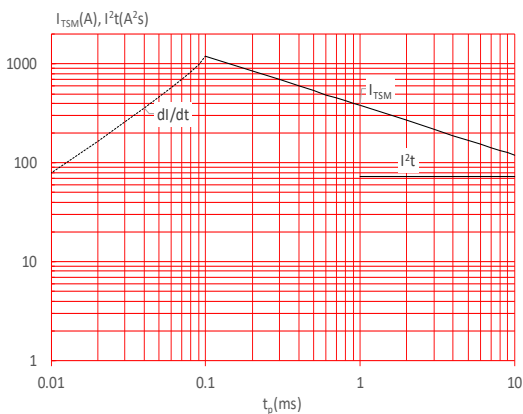


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

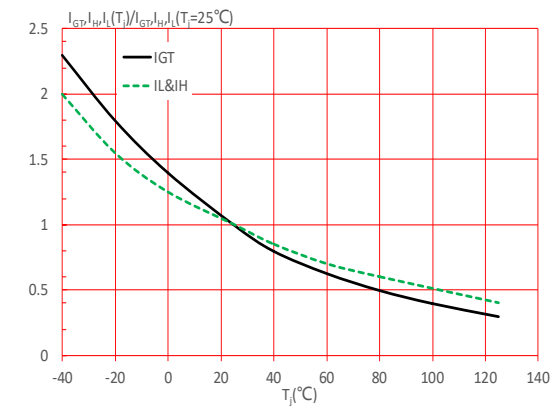
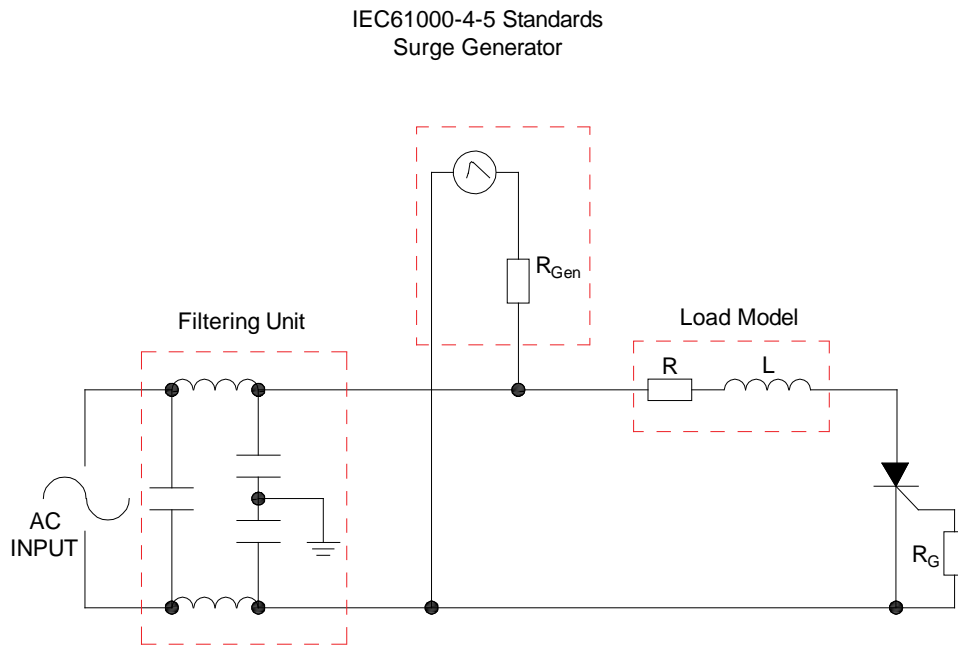


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

ORDERING INFORMATION

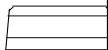
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
BT151	650	15	TO-220B(Non-Ins)	50	Tube

Document Revision History

Date	Revision	Changes
May.04, 2023	A.1.0	Last update

BT151

PACKAGE M



TEL +86-513-

